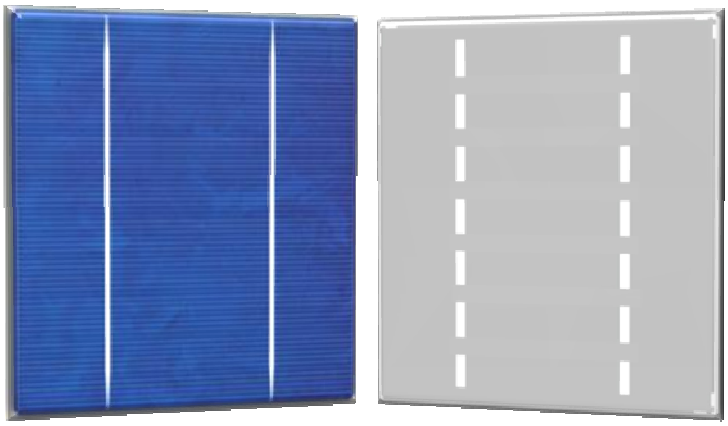
Specification					
Technical Data sheet					
DMS loc.: 8100.03E	Rev.: 03	Doc.: FO	Rev. date: 28-05-2013	Doc. owner: QA	Physical location:
Cell Type: H-pattern / segmented Back-side Configuration 08					

Description



Cell Layout H_GEN_02

Dimensions		
Feature	**Qualification**	**Permitted Deviation**
Outer dimensions	156mm x 156mm	± 0.5 mm
Cell thickness nominal as ordered	on wafer level	± 30 µm
Bow 	Cell placed on flat surface sunny side up. Distance between centre of cell and flat surface	<= 2.5mm.

Front surface		
Width of busbar	1.8 mm	± 0.1 mm
Number of busbar	2	
Distance between the centre lines of busbar	75.0	± 0.2 mm
Material of busbar	Silver	

Back surface		
Width of busbar	4 mm	± 0.5 mm
Number of segments	8	
Length of segment interruption	6 mm	± 0.5 mm
Number of busbar	2	
Distance between the centre lines of busbar	75.0	± 0.2 mm
Material of busbar	Silver	
Material of the surrounding parts of the back surface of the cell	Aluminum	

Electrical properties		
Power	Power classes according to P_{max} at standard test conditions (STC, AM 1.5, 1000 W/m^2, 25°C) Accuracy of measurement ± 1.5% relative to ISE certified reference cell	Divided in classes, see below
Reverse bias criteria	Reverse dark measurement V_{bias}= -12 V allowed current V_{bias}= -6 V allowed current measurement accuracy ± 2%	 I bias <2.0 A, I bias <0.4 A.
Shunt resistivity	(Dark I-V measurement) at 0V	R_{sh}> 15 Ohm

Typical data at STC (non encapsulated cells)*

Cellclass	Pmpp(W)	Efficiency(%)	Voc(mV)	Isc(A)
S156PS355	3.55	14.60	604	7.69
S156PS360	3.60	14.80	606	7.74
S156PS365	3.65	15.00	607	7.80
S156PS370	3.70	15.20	610	7.86
S156PS375	3.75	15.40	613	7.92
S156PS380	3.80	15.60	615	7.98
S156PS385	3.85	15.80	618	8.04
S156PS390	3.90	16.00	619	8.14
S156PS395	3.95	16.20	620	8.22
S156PS400	4.00	16.40	622	8.28
S156PS405	4.05	16.60	625	8.35
S156PS410	4.10	16.80	627	8.41
S156PS415	4.15	17.00	630	8.47
S156PS420	4.20	17.20	632	8.53